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Kind regards,

Team Nexperia

PEMB2; PUMB2

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Rev. 3 — 17 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number			NPN/PNP	NPN/NPN	Package	
	NXP	JEITA	complement	complement	configuration	
PEMB2	SOT666	-	PEMD12	PEMH2	ultra small and flat lead	
PUMB2	SOT363	SC-88	PUMD12	PUMH2	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	[6] [5] [4]	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa21

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMB2	-	plastic surface-mounted package; 6 leads	SOT666	
PUMB2	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMB2	B2
PUMB2	B*2

[1] * = placeholder for manufacturing site code

5. Limiting values

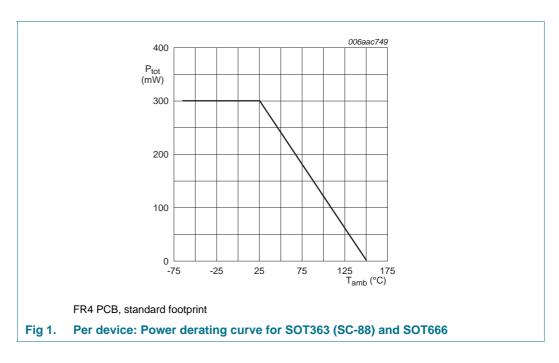
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	tor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-40	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMB2 (SOT666)		[1][2]	200	mW
	PUMB2 (SOT363)		<u>[1]</u> _	200	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMB2 (SOT666)		[1][2] _	300	mW
	PUMB2 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



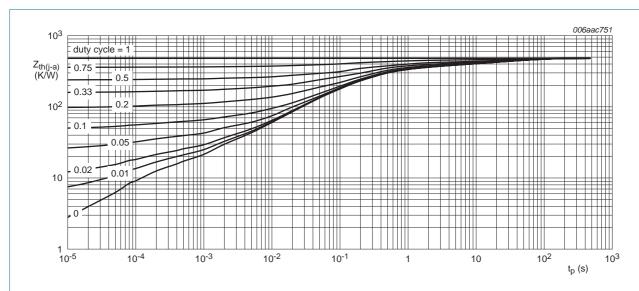
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB2 (SOT666)		[1][2]	-	625	K/W
	PUMB2 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB2 (SOT666)		[1][2] -	-	417	K/W
	PUMB2 (SOT363)		<u>[1]</u> _	-	417	K/W

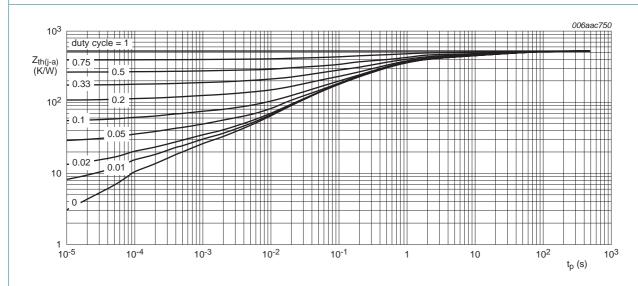
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB2 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB2 (SOT363); typical values

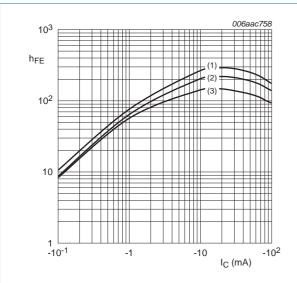
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-90	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = -5 V; I_{C} = -100 μA	-	-1.2	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-3	-1.6	-	V
R1	bias resistor 1 (input)		33	47	61	$k\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

^[1] Characteristics of built-in transistor



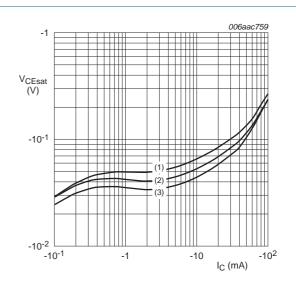
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



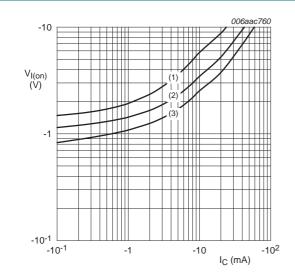
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



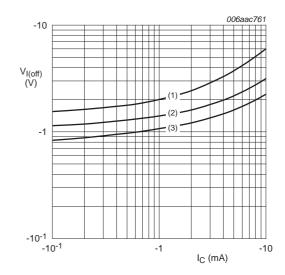
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



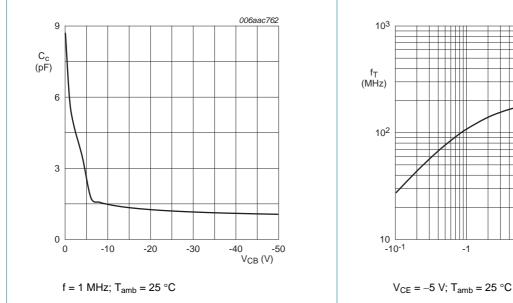
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

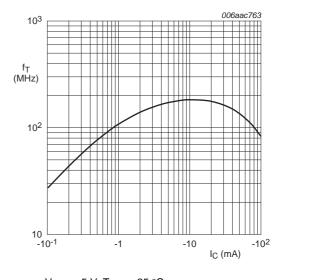
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values



Collector capacitance as a function of Fig 8. collector-base voltage; typical values of built-in transistor



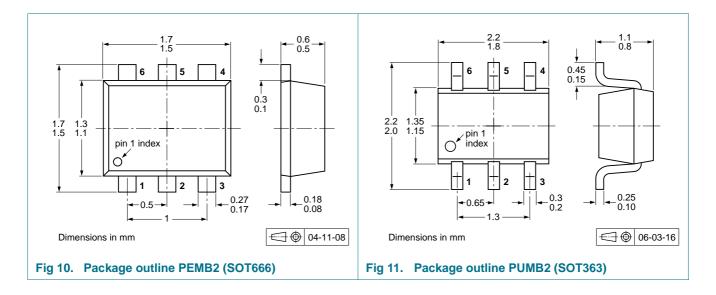
Transition frequency as a function of collector Fig 9. current; typical values of built-in transistor

Test information 8.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Package outline 9.



PEMB2 PUMB2

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10. Packing information

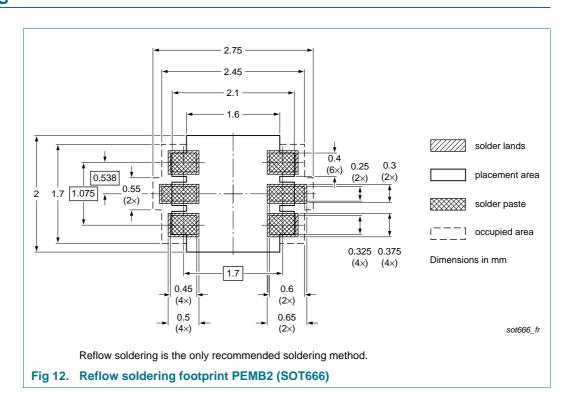
Table 9. Packing methods

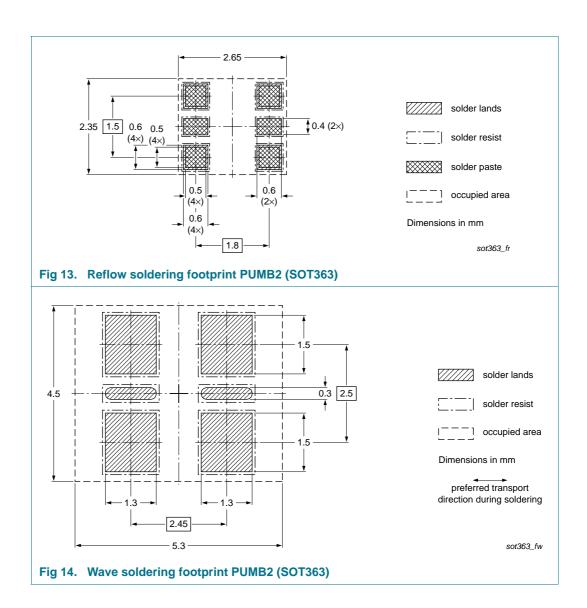
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Description		Packing quantity				
number			3000	4000	8000	10000		
PEMB2	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-		
	4 mm pitch, 8 mm tape and reel	-	-115	-	-			
PUMB2	SOT363	4 mm pitch, 8 mm tape and reel; T1	1 -115	-	-	-135		
		4 mm pitch, 8 mm tape and reel; T2	125	-	-	-165		

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





12. Revision history

Table 10. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB2_PUMB2 v.3	20111117	Product data sheet	-	PEMB2_PUMB2 v.2
Modifications:	guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate Section 1 "Product profile": updated Section 4 "Marking": updated Figure 1 to 9: added			
	 Section 6 " Table 8 "Cl to V_{I(off)} off Section 8 " 	Limiting values": updated Thermal characteristics": upharacteristics": Vi(on) redefined the state input voltage, ICEO upterst information": added the spackage outline": supersections.	ed to $V_{I(on)}$ on-state inputated, f_T added	. ,
	Section 11	"Packing information": add "Soldering": added "Legal information": update		
PEMB2_PUMB2 v.2	20031015	Product data sheet	-	PUMB2 v.1 PEMB2 v.1
PEMB2 v.1	20010914	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB2_PUMB2

PEMB2; PUMB2

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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